

Schottky barrier diode

RB161L-40

● Applications

High frequency rectification
For switching power supply

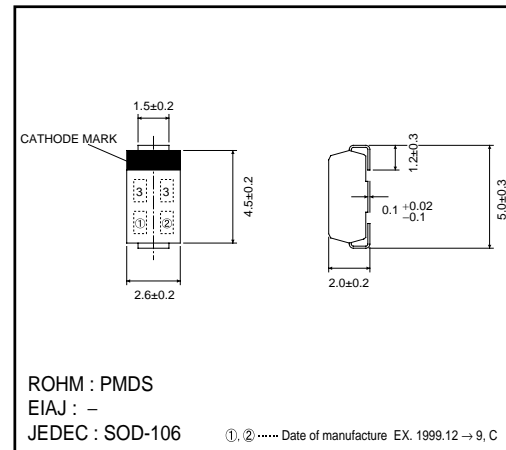
● Features

- 1) Compact power mold type. (PMDS)
- 2) Ultra low V_F . ($V_F=0.35V$ Typ. at 1A)
- 3) $V_{RM}=40V$ guaranteed.

● Construction

Silicon epitaxial planar

● External dimensions (Units : mm)



● Absolute maximum ratings ($T_a=25^\circ C$)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	20	V
Mean rectifying current *	I_o	1	A
Peak forward surge current	I_{FSM}	70	A
Junction temperature	T_j	125	$^\circ C$
Storage temperature	T_{stg}	-40→+125	$^\circ C$

* When mounting on PCB

● Electrical characteristics ($T_a=25^\circ C$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.40	V	$I_F=1.0A$
Reverse current	I_R	-	-	1	mA	$V_R=20V$

Diodes

● Electrical characteristic curves (Ta=25°C)

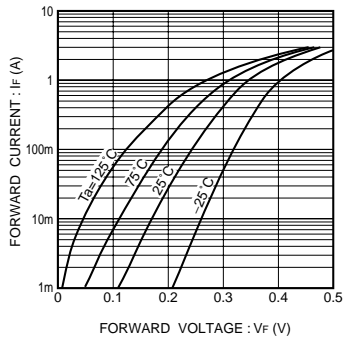


Fig.1 Forward characteristics

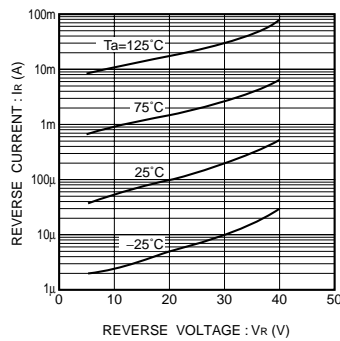


Fig.2 Reverse characteristics

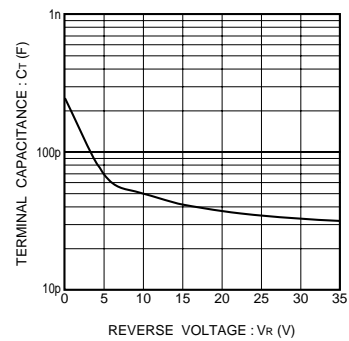


Fig.3 Capacitance between terminals characteristics

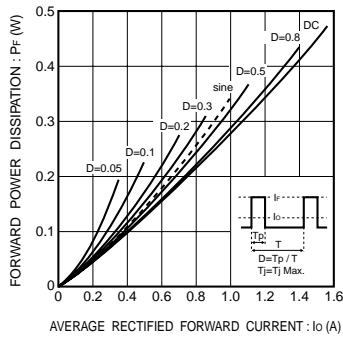


Fig.4 Forward power dissipation characteristics

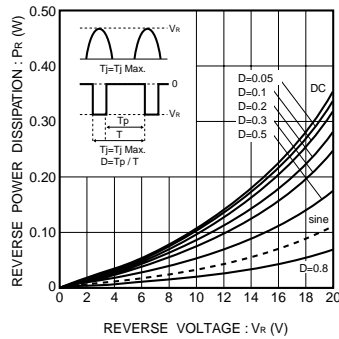


Fig.5 Reverse power dissipation characteristics

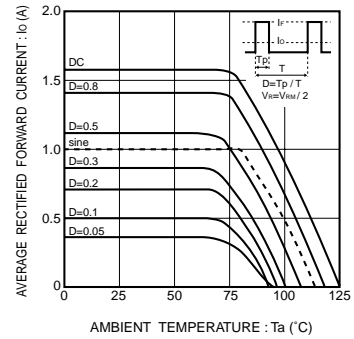


Fig.6 Derating curve (when mounting on glass epoxy PCBs)